

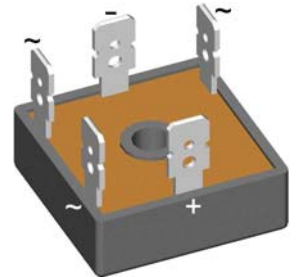
## Standard Rectifier Module

<b>3~ Rectifier</b>	
$V_{RRM}$	= 1200 V
$I_{DAV}$	= 20 A
$I_{FSM}$	= 380 A

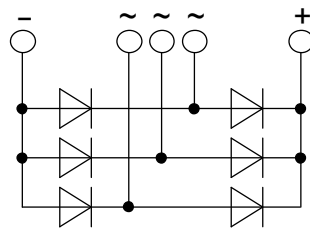
### 3~ Rectifier Bridge

Part number

VUO25-12NO8



 E72873



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

#### Applications:

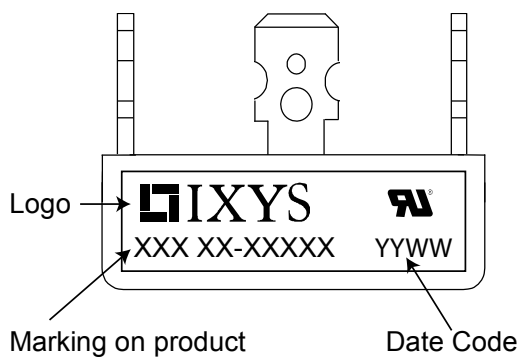
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

#### Package: FO-B

- Industry standard outline
- RoHS compliant
- ¼" fast-on terminals
- Easy to mount with one screw

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1200	V
$I_R$	reverse current	$V_R = 1200$ V	$T_{VJ} = 25^\circ\text{C}$			40	$\mu\text{A}$
		$V_R = 1200$ V	$T_{VJ} = 150^\circ\text{C}$			1.5	mA
$V_F$	forward voltage drop	$I_F = 10$ A	$T_{VJ} = 25^\circ\text{C}$			1.05	V
		$I_F = 30$ A				1.25	V
		$I_F = 10$ A	$T_{VJ} = 125^\circ\text{C}$			0.94	V
		$I_F = 30$ A				1.21	V
$I_{DAV}$	bridge output current	$T_C = 85^\circ\text{C}$ rectangular	$T_{VJ} = 150^\circ\text{C}$ $d = \frac{1}{3}$			20	A
$V_{FO}$	threshold voltage	} for power loss calculation only				0.77	V
$r_F$	slope resistance					14.2	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					8	K/W
$R_{thCH}$	thermal resistance case to heatsink					1	K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		15	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			380	A
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			410	A
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			325	A
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			350	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			720	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			700	A <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			530	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			510	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz	$T_{VJ} = 25^\circ\text{C}$		10		pF

Package FO-B		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			100	A
$T_{stg}$	storage temperature		-40		125	°C
$T_{VJ}$	virtual junction temperature		-40		150	°C
<b>Weight</b>				20		g
$M_D$	mounting torque		1.8		2.2	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	9.0	7.0		mm
$d_{Spb/Apb}$		terminal to backside	10.0	10.0		mm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500			V

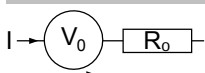


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO25-12NO8	VUO25-12NO8	Box	50	465100

### Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 150^\circ\text{C}$



Rectifier

$V_{0\max}$	threshold voltage	0.77	V
$R_{0\max}$	slope resistance *	13	mΩ



Rectifier

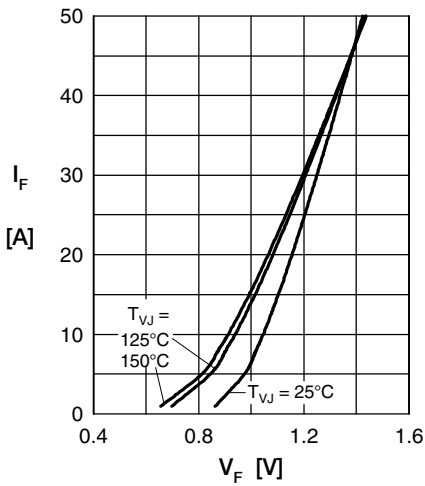


Fig. 1 Forward current vs. voltage drop per diode

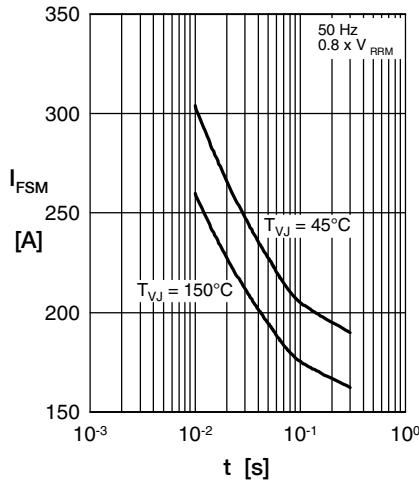


Fig. 2 Surge overload current vs. time per diode

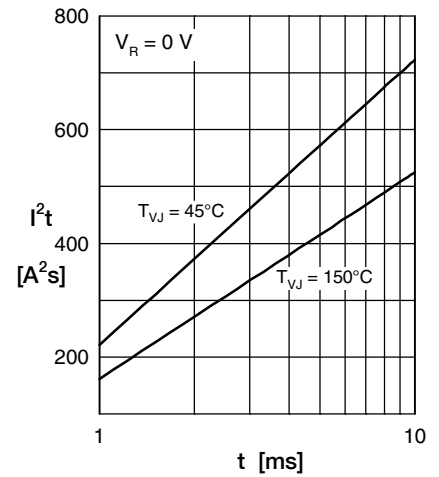


Fig. 3 I<sup>2</sup>t vs. time per diode

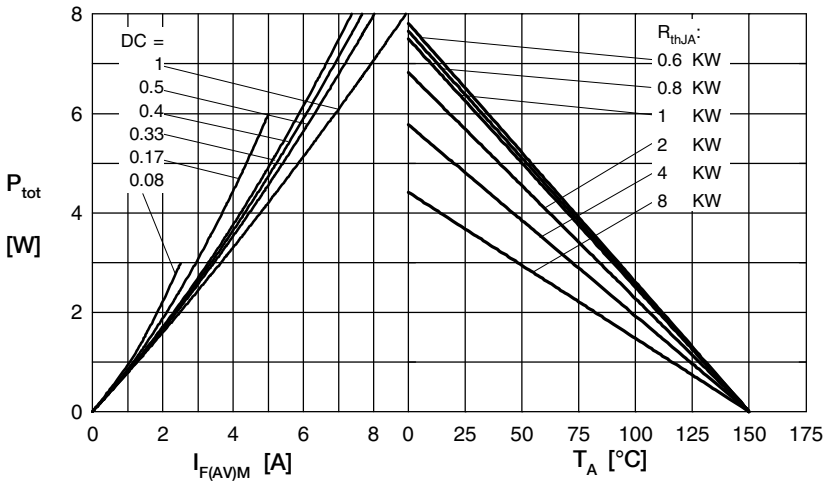


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

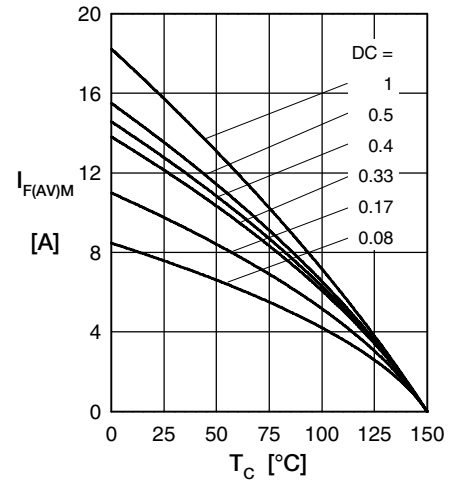


Fig. 5 Max. forward current vs. case temperature per diode

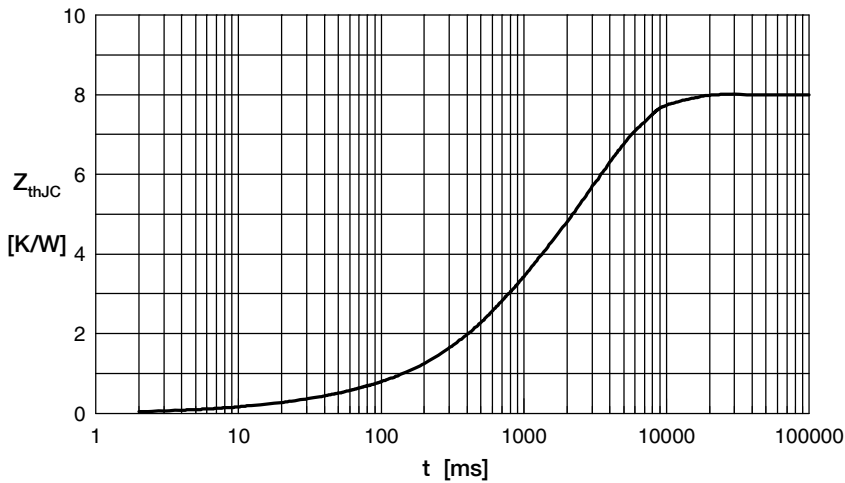


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z<sub>thJC</sub> calculation:

i	R <sub>th</sub> (K/W)	t <sub>i</sub> (s)
1	0.040	0.005
2	0.250	0.030
3	1.810	0.500
4	5.900	3.200

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